

ABSTRACT OF THE DISCLOSURE

A method of forming contact for a semiconductor device is disclosed. The method has the steps of forming
5 a first interlayer dielectric layer on a silicon substrate; forming a conductive material pattern on a portion of the first interlayer dielectric layer; forming a second interlayer dielectric layer over the first interlayer dielectric layer and over the
10 conductive material pattern; forming first and second contact holes by selectively and sequentially removing the second and the first interlayer dielectric layers, the depth of the second contact hole being greater than a depth of the first contact hole, the first contact hole
15 exposing a portion of the conductive material pattern, and the second contact hole exposing a portion of the silicon substrate; forming a glue layer on the first and the second interlayer dielectric layers including over the first and the second contact holes, the glue layer
20 including a CVD TiN layer; and filling the first and the second contact holes with a tungsten layer by forming the tungsten layer on the glue layer.